BYV25FX-600 Enhanced ultrafast power diode Rev. 02 — 7 March 2011



Product data sheet

Product profile 1.

1.1 General description

Enhanced ultrafast power diode in a SOD113 (2-lead TO-220F) plastic package.

1.2 Features and benefits

- High thermal cycling performance
- Isolated package
- Low on-state losses

- Low thermal resistance
- Soft recovery characteristic

1.3 Applications

■ Dual Mode (DCM and CCM) PFC

■ Power Factor Correction (PFC) for Interleaved Topology

1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; $\delta = 0.5$; $T_h \le 97$ °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	5	Α
Static char	acteristics					
V _F	forward voltage	$I_F = 5 \text{ A}; T_j = 25 \text{ °C};$ see Figure 5	-	1.3	1.9	V
		$I_F = 5 \text{ A}$; $T_j = 150 \text{ °C}$; see Figure 5	-	1.1	1.7	V
Dynamic c	haracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 6	-	17.5	35	ns



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
F 111	-	-	Simplified Outlifie	Grapino Symbol
1	K	cathode		v 14 A
2	Α	anode	mb	K
mb	n.c.	mounting base; isolated		
			SOD113 (TO-220F)	

3. Ordering information

Table 3. Ordering information

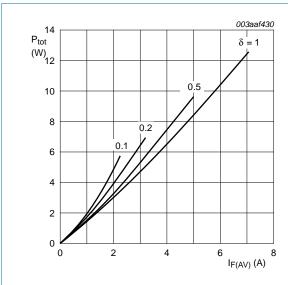
Type number	Package		
	Name	Description	Version
BYV25FX-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

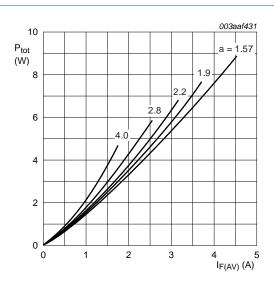
Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; $\delta = 0.5$; $T_h \le 97$ °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	5	A
I _{FRM}	repetitive peak forward current	square-wave pulse; δ = 0.5 ; t_p = 25 μ s; $T_h \le$ 97 °C	-	10	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; see <u>Figure 3</u>	-	60	Α
		t _p = 8.3 ms; sine-wave pulse; T _{j(init)} = 25 °C; see <u>Figure 3</u>	-	66	Α
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C



$$I_{F(AV)} = I_{F(RMS)} imes \sqrt{oldsymbol{\delta}}$$

 $V_0 = 1.499 \text{ V}; R_S = 0.041 \Omega$

Fig 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



 $a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$

 $V_o = 1.499 \text{ V}; R_s = 0.041 \Omega$

Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

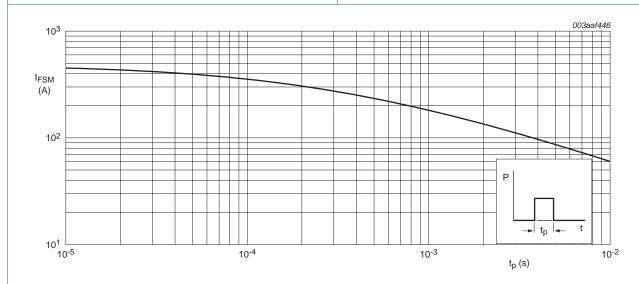


Fig 3. Non-repetitive peak forward current as a function of pulse width; square waveform; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 4	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W

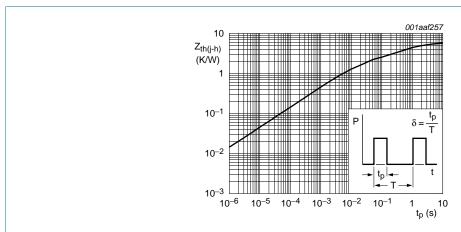


Fig 4. Transient thermal impedance from junction to heatsink as a function of pulse width

6. Isolation characteristics

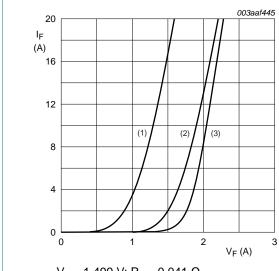
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	pF

Characteristics

Table 7. **Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
Static charac	Static characteristics							
V _F	forward voltage	$I_F = 5 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 5}}{}$	-	1.3	1.9	V		
		$I_F = 5 \text{ A}; T_j = 150 \text{ °C}; \text{ see } \frac{\text{Figure 5}}{}$	-	1.1	1.7	V		
I_R	reverse current	V _R = 600 V; T _j = 100 °C	-	-	1.5	mA		
		$V_R = 600 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	50	μA		
Dynamic cha	racteristics							
Q _r	recovered charge	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 6	-	13	-	nC		
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 6	-	17.5	35	ns		
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 6	-	1.5	-	Α		
V_{FRM}	forward recovery voltage	$I_F = 1 \text{ A}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 7	-	3.2	-	V		



 $V_o = 1.499 \text{ V}; R_s = 0.041 \Omega$

(1) T_j = 150 °C; typical values;

(2) T_i = 150 °C; maximum values;

(3) $T_j = 25$ °C; maximum values;

Fig 5. Forward current as a function of forward voltage

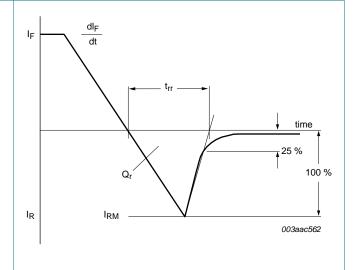
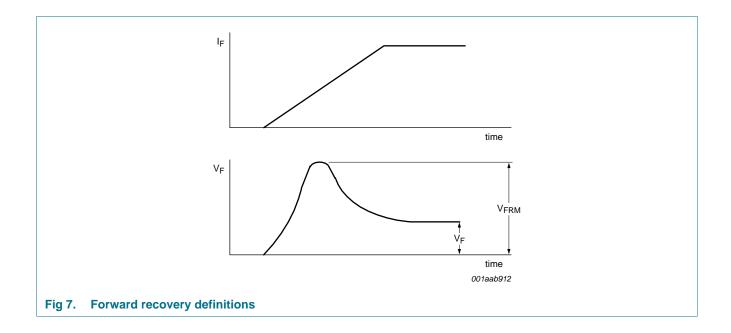


Fig 6. Reverse recovery definitions; ramp recovery



Package outline

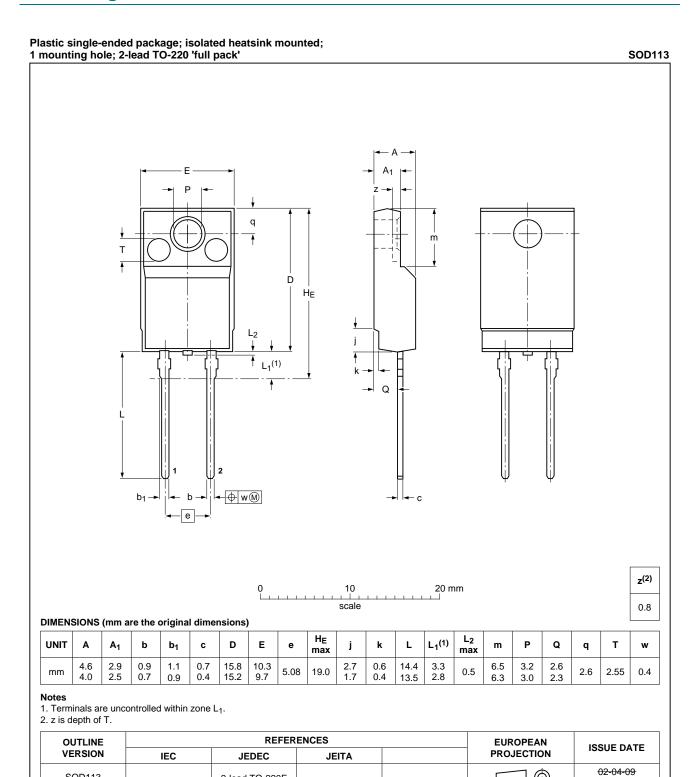


Fig 8. Package outline SOD113 (TO-220F)

Product data sheet

SOD113

07-06-18

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2-lead TO-220F



9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV25FX-600 v.2	20110307	Product data sheet	-	BYV25FX-600 v.1
Modifications:	 Various chang 	es to content.		
BYV25FX-600 v.1	20101004	Product data sheet	-	-

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10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Product data sheet

BYV25FX-600

Enhanced ultrafast power diode

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